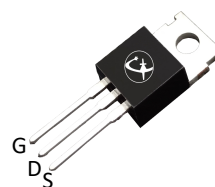
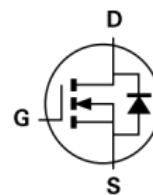


MAIN CHARACTERISTICS

I_D	130A
V_{DSS}	150V
$R_{DS(on)-typ}$ (@ $V_{GS}=10V$ $T_c=25^{\circ}C$)	5.2m Ω



TO-220C

FEATURES

- Ultra-Low $R_{DS(ON)}$
- Low Gate Charge
- High Current Capability

APPLICATIONS

- Power Management in Telecom., Industrial Automatic
- Motor Driving in Power Tool, E-vehicle, Robotics
- Current Switching in DC/DC&AC/DC(SR) Sub-system

MECHANICAL DATA

- Case: Molded plastic
- Mounting Position: Any

Product specification classification

Part Number	Package	Mode Name	Pack
LG130N15AP	TO-220C	LG130N15AP	Tube

Maximum Ratings at Tc=25°C unless otherwise specified

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	150	V
Gate-Source Voltage	V_{GS}	± 20	V
Continue Drain Current	I_D	130	A
Pulsed Drain Current (Note1)	I_{DM}	190	A
Power Dissipation	P_D	240	W
Single Pulse Avalanche Energy (Note1)	E_{AS}	864	mJ
Operating Temperature Range	T_J	150	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.52	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	45	°C/W

Note1:Pulse test: 300 μ s pulse width, 2 % duty cycle

Electrical Characteristics at Tc=25°C unless otherwise specified

Parameter	Test Condition	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	BV_{DSS}	150	-	-	V
Drain-Source Leakage Current	$V_{DS} = 120 \text{ V}, V_{GS} = 0 \text{ V}$	I_{DSS}	-	-	1	μA
Gate Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	I_{GSS}	-	-	± 100	nA
Gate-Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	$V_{GS(th)}$	2.5	-	4.5	V
Drain-Source On-State Resistance	$V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	$R_{DS(on)}$	-	5.2	6.5	m Ω
Forward Transconductance	$V_{DS} = 5 \text{ V}, I_D = 20 \text{ A}$	g_{fs}	-	51	-	S
Input Capacitance	$V_{GS} = 0 \text{ V}, V_{DS} = 75 \text{ V}, f = 1 \text{ MHz}$	C_{iss}	-	5800	-	pF
Output Capacitance		C_{oss}	-	557	-	pF
Reverse Transfer Capacitance		C_{rss}	-	16.8	-	pF
Turn-on Delay Time(Note2)	$V_{GS}=10\text{V}, V_{DD}=75 \text{ V}, R_G=3 \Omega, R_L=3.75 \Omega$	$t_{d(ON)}$	-	21	-	ns
Rise Time(Note2)		t_r	-	39	-	ns
Turn-Off Delay Time(Note2)		$t_{d(OFF)}$	-	63	-	ns
Fall Time(Note2)		t_f	-	32	-	ns
Total Gate Charge(Note2)	$I_D = 20 \text{ A}, V_{DD} = 75 \text{ V}, V_{GS} = 10 \text{ V}$	Q_G	-	83	-	nC
Gate to Source Charge(Note2)		Q_{GS}	-	28	-	nC
Gate to Drain Charge(Note2)		Q_{GD}	-	19.2	-	nC

Source-Drain Diode Characteristics at Ta=25°C unless otherwise specified

Parameter	Test Condition	Symbol	Min.	Typ.	Max.	Unit
Maximun Body-Diode Continuous Current		I_S	-	-	130	A
Maximun Body-Diode Pulsed Current(Note2)		I_{SM}	-	-	190	A
Drain-Source Diode Forward Voltage	$I_{SD} = 1 \text{ A}$	V_{SD}	-	-	1.2	V
Reverse Recovery Time(Note2)	$I_{SD} = 15 \text{ A}, V_{GS} = 0 \text{ V}, dI_F / dt = 100 \text{ A}/\mu\text{s}$	t_{rr}	-	98	-	ns
Reverse Recovery Charge(Note2)		Q_{rr}	-	316	-	nC

Note2:Pulse test: 300 μ s pulse width, 2 % duty cycle

RATINGS AND CHARACTERISTIC CURVES

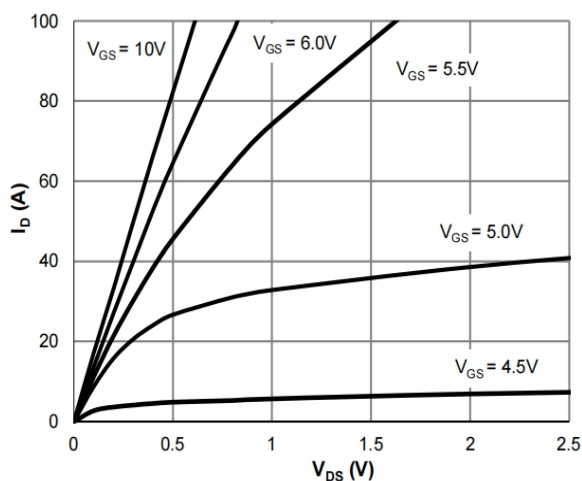


Figure 1: Saturation Characteristics

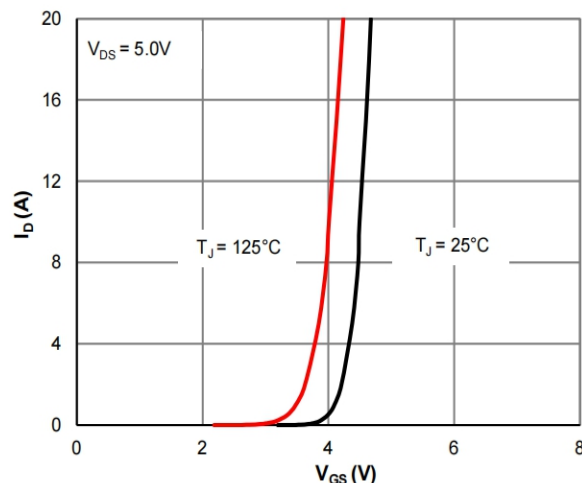


Figure 2: Transfer Characteristics

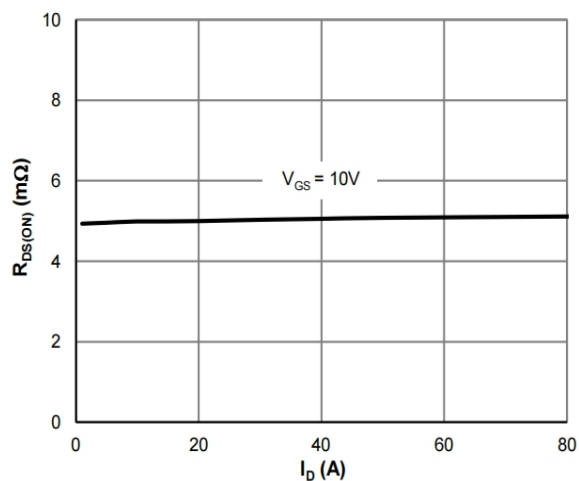


Figure 3: $R_{DS(ON)}$ vs. Drain Current

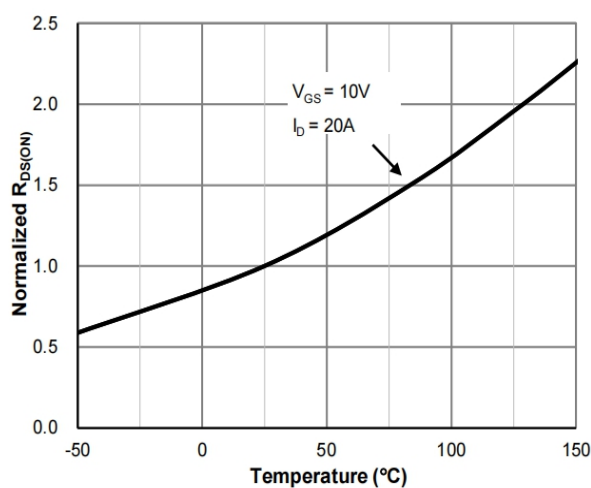


Figure 4: $R_{DS(ON)}$ vs. Junction Temperature

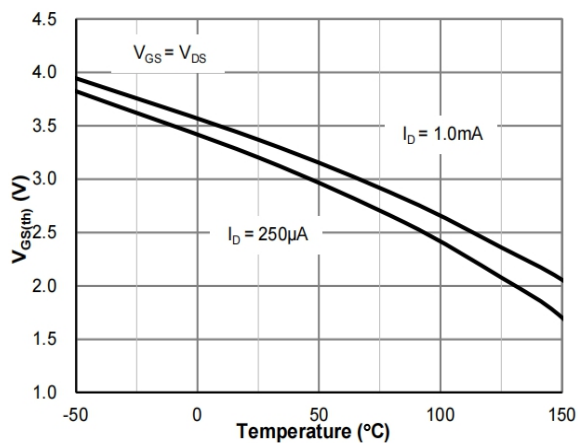


Figure 5: $V_{GS(th)}$ vs. Junction Temperature

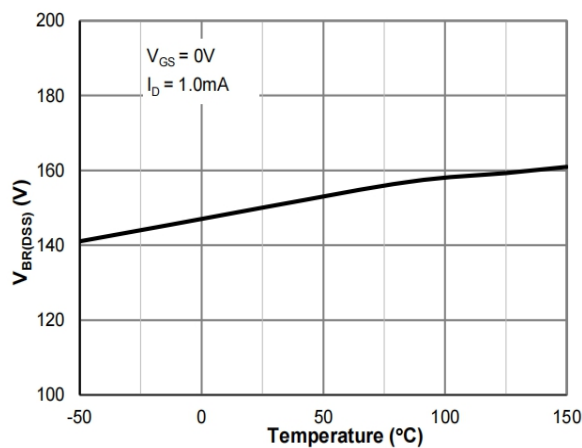


Figure 6: $V_{BR(DSS)}$ vs. Junction Temperature

RATINGS AND CHARACTERISTIC CURVES

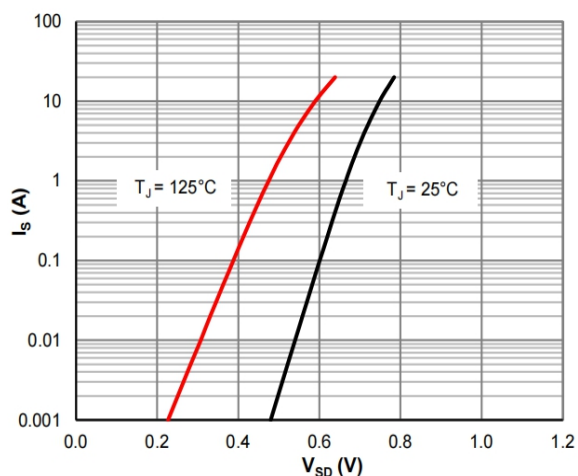


Figure 7: Body-Diode Characteristics

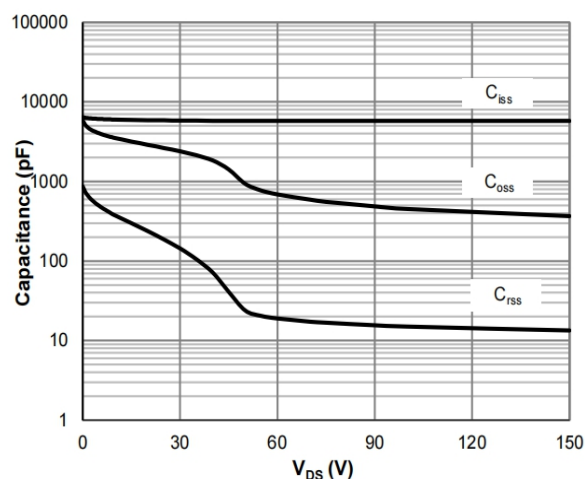


Figure 8: Capacitance Characteristics

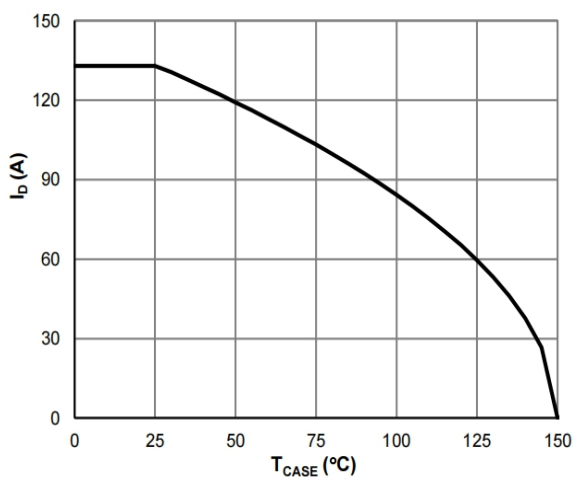


Figure 9: Current De-rating

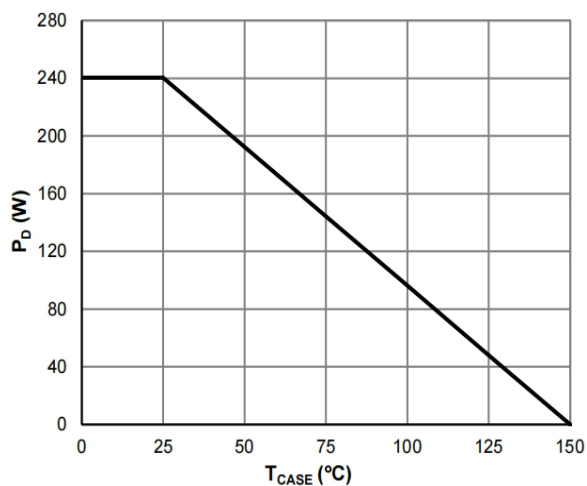


Figure 10: Power De-rating

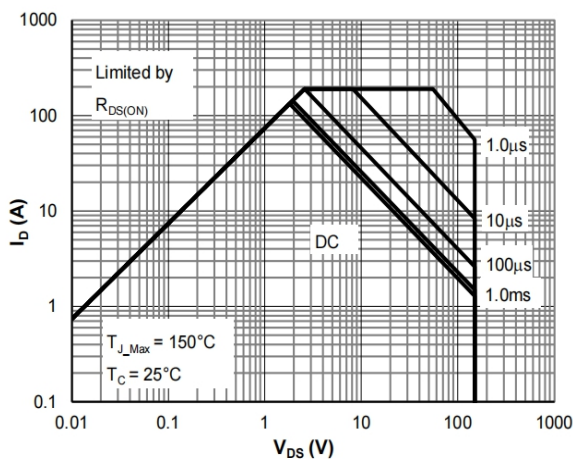


Figure 11: Maximum Safe Operating Area

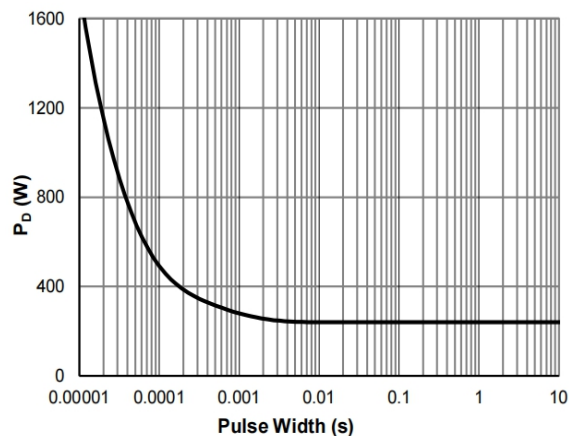
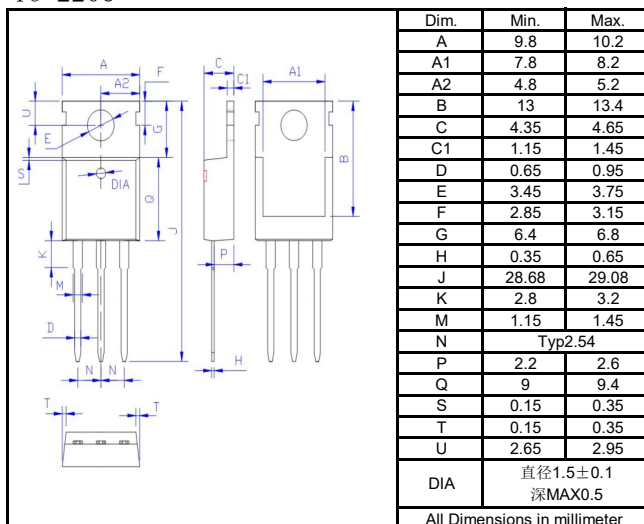


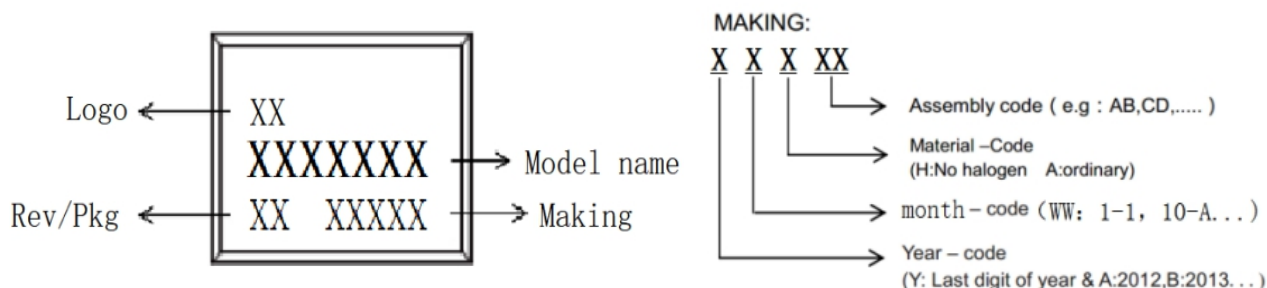
Figure 12: Single Pulse Power Rating, Junction-to-Case

Package Outline Dimensions millimeters

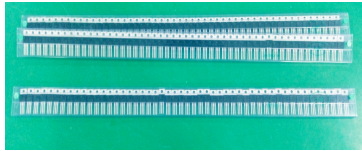
TO-220C



Marking on the body



packing instruction

PKG	Minimal Package	Mini Box	Box
TO-220C			
	50pcs/pdpe	1000pcs/box	5000pcs/box



LG130N15AP

N-Channel SGT Power MOSFET

Notice

All product, product specifications and data are subject to change without notice to improve. The right to explain is owned by LINGXUN electronics company.

Confirm that operation temperature is within the specified range described in the product specification. Avoid applying power exceeding normal rated

power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.

LINGXUN electronics shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

<http://www.lxmicro.com>

Revision History

Rev	Changes	Date
1.0	First version	2025/6/9